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View Online at https://aerobasegroup.com/nsn/5961-01-043-1076
Inclosure Material:
Metal
Overall Length:
Between 0.250 inches and 0.360 inches
Terminal Length:
Between 0.312 inches and 0.500 inches
Overall Diameter:
0.875 inches
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
То-3
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Terminal and unthreaded hole
Terminal Circle Diameter:
0.430 inches
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
275.0 breakdown voltage, collector-to-base, emitter open and 250.0 breakdown voltage, collector-to-emitter, base open and 6.0
breakdown voltage, emitter-to-base, collector open
Current Rating Per Characteristic:
20.00 amperes source cutoff current
Power Rating Per Characteristic:
150.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: npn
Test Data Document:
06481-6020016 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
1 case and 2 pin
Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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